ABSTRACT

A semiconductor device comprising a first semiconductor region and a second semiconductor region,

(a) wherein a field effect transistor is comprised of the first semiconductor region comprising at least one semiconductor layer(s) protruding upward from a substrate, a gate electrode(s) formed via an insulating film such that the gate electrode(s) strides over the semiconductor layer(s) and source/drain regions provided in the semiconductor layer(s) on both sides of the gate electrode(s),whereby a channel region is formed in at least both sides of the semiconductor layer(s),

(b) wherein the second semiconductor region comprises semiconductor layers protruding upward from the substrate and placed, at least opposing the first semiconductor region at both ends in the direction perpendicular to a channel current direction and the side surface of the semiconductor layers facing the first semiconductor region is parallel to the channel current direction.